



# BC857BV

### PNP DUAL SMALL SIGNAL SURFACE MOUNT **TRANSISTOR**

WWW.DZ

### **Features**

**Epitaxial Die Construction** 

Complementary NPN Types Available (BC847BV)

Ultra-Small Surface Mount Package

Lead Free By Design/RoHS Compliant (Note 3)

### **Mechanical Data**

Case: SOT-563

Case Material: Molded Plastic. UL Flammability

Classification Rating 94V-0

Moisture sensitivity: Level 1 per J-STD-020C

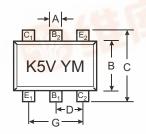
Terminal Connections: See Diagram

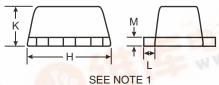
Terminals: Finish - Matte Tin annealed over Alloy 42 leadframe. Solderable per MIL-STD-202, Method 208

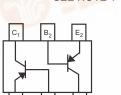
Marking (See Page 2): K5V

Ordering & Date Code Information: See Page 2

Weight: 0.003 grams (approximate)







	SOT-563										
Dim	Min	Max	Тур								
Α	0.15	0.30	0.25								
В	1.10	1.25	1.20								
С	1.55 1.70 1.60										
D	0.50										
G	0.90	1.10	1.00								
Н	1.50	1.70	1.60								
K	0.56	0.60	0.60								
L	0.10	0.30	0.20								
M	0.10 0.18 0.1										
All	All Dimensions in mm										

## Maximum Ratings @ T<sub>A</sub> = 25°C unless otherwise specified

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V <sub>CBO</sub>	-50	V
Collector-Emitter Voltage	V <sub>CEO</sub>	-45	V
Emitter-Base Voltage	V <sub>EBO</sub>	-5.0	V
Collector Current	Ic	-100	mA
Power Dissipation (Note 2)	P <sub>d</sub>	150	mW
Thermal Resistance, Junction to Ambient (Note 2)	R JA	833	°C/W
Operating and Storage Temperature Range	T <sub>j</sub> , T <sub>STG</sub>	-55 to +150	°C

Notes:

- Device mounted on FR-4 PCB, 1 inch x 0.85 inch x 0.062 inch; pad layout as shown on Diodes Inc. suggested pad layout document AP02001, which can be found on our website at http://www.diodes.com/datasheets/ap02001.pdf.
  No purposefully added lead.





# **Electrical Characteristics** @ T<sub>A</sub> = 25°C unless otherwise specified

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
Collector-Base Breakdown Voltage	(Note 4)	V <sub>(BR)CBO</sub>	-50	_	_	٧	I <sub>C</sub> = 10 A, I <sub>B</sub> = 0
Collector-Emitter Breakdown Voltage	(Note 4)	V <sub>(BR)CEO</sub>	-45	_	_	٧	I <sub>C</sub> = 10mA, I <sub>B</sub> = 0
Emitter-Base Breakdown Voltage	(Note 4)	V <sub>(BR)EBO</sub>	-5	_	_	V	I <sub>E</sub> = 1 A, I <sub>C</sub> = 0
DC Current Gain	(Note 4)	h <sub>FE</sub>	220	290	475	_	$V_{CE} = -5.0V, I_{C} = -2.0mA$
Collector-Emitter Saturation Voltage	(Note 4)	V <sub>CE(SAT)</sub>	_	_	-100 -400	mV	I <sub>C</sub> = -10mA, I <sub>B</sub> = -0.5mA I <sub>C</sub> = -100mA, I <sub>B</sub> = -5.0mA
Base-Emitter Saturation Voltage	(Note 4)	V <sub>BE(SAT)</sub>		-700 -900	_	mV	I <sub>C</sub> = -10mA, I <sub>B</sub> = -0.5mA I <sub>C</sub> = -100mA, I <sub>B</sub> = -5.0mA
Base-Emitter Voltage	(Note 4)	V <sub>BE(ON)</sub>	-600 —	=	-750 -820	mV	V <sub>CE</sub> = -5.0V, I <sub>C</sub> = -2.0mA V <sub>CE</sub> = -5.0V, I <sub>C</sub> = -10mA
Collector-Cutoff Current	(Note 4)	I <sub>CBO</sub>		_	-15 -4.0	nΑ μΑ	V <sub>CB</sub> = -30V V <sub>CB</sub> = -30V, T <sub>A</sub> = 150°C
Gain Bandwidth Product		fT	100	_	_	MHz	V <sub>CE</sub> = -5.0V, I <sub>C</sub> = -10mA, f = 100MHz
Output Capacitance		Сов	_	_	4.5	pF	V <sub>CB</sub> = -10V, f = 1.0MHz
Noise Figure		NF	_	_	10	dB	$\label{eq:local_local_local_local_local} \begin{split} I_C &= \text{-0.2mA}, \ V_{CE} = \text{-5.0Vdc}, \\ R_S &= 2.0 \text{K}  , \ f = 1.0 \text{KHz}, \\ \text{BW} &= 200 \text{Hz} \end{split}$

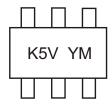
# **Ordering Information** (Note 5)

Device	Packaging	Shipping		
BC857BV-7	SOT-563	3000/Tape & Reel		

Notes:

- 4. Short duration pulse test used to minimize self-heating effect.
- 5. For Packaging Details: go to our website at http://www.diodes.com/datasheets/ap02007.pdf.

# **Marking Information**



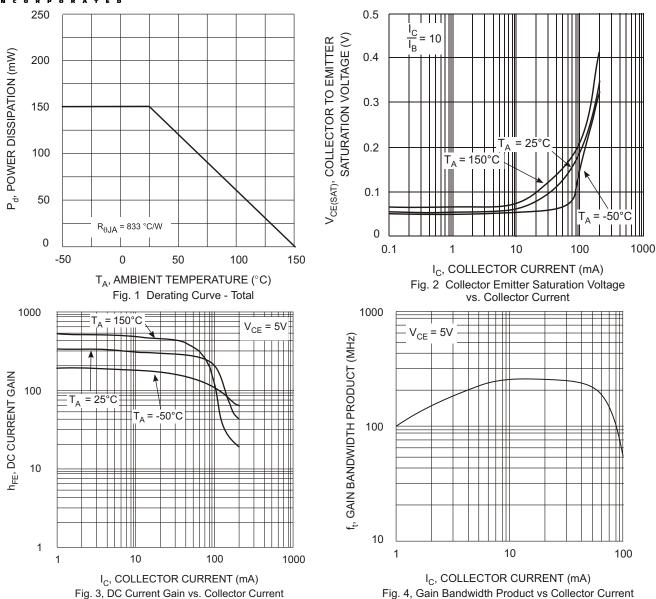
K5V = Product Type Marking Code YM = Date Code Marking Y = Year (ex: T = 2006) M = Month (ex: 9 = September)

#### Date Code Key

Year	2003	2004	2005	2006	2007	2008	2009	2010	2011	2012
Code	Р	R	S	Т	U	V	W	X	Υ	Z

Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D





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